AMENDMENTS TO THE CLAIMS:

Please amend claims 1 and 2 as follows.

Please add new claims 6-14 as follows.

1. (Currently Amended) A method of forming a device isolation film in a semiconductor device, comprising the steps of:

performing an ion implantation for controlling a threshold voltage on a surface of a semiconductor substrate;

forming a trench having a side wall to define an active region and a device isolation region by ~~performing a photolithography process on~~ etching a portion of the semiconductor substrate of a device isolation region;

forming a side wall oxidation film at the side wall of the trench by performing an oxidation process at a temperature for extremely prohibiting ions, which are implanted to control the threshold voltage, from diffusing to the device isolation region ~~and forming a side wall oxidation film at the side wall of the trench~~;

performing an ion implantation ~~on the active region~~ to compensate for ions for controlling the threshold voltage, which are diffused from the active region to the side wall oxidation film by the oxidation process; and

forming a device isolation film by burying the oxidation film inside the trench.

2. (Currently Amended) The method of claim 1, ~~wherein, when forming the trench,~~ comprising forming the side wall oxidation film ~~is formed~~ to perform a rounding treatment on an upper portion or a bottom corner of the trench and to increase an adhesive strength of the oxidation film to be buried inside the trench, at the same time, and the film is formed to a thickness in the range of about 50 Å to 100 Å.

3. (Currently Amended) The method of claim 1, ~~wherein~~ comprising performing the oxidation process ~~is performed~~ by a dry oxidation method at a temperature in the range of about 800℃ to 950℃.

4. (Currently Amended) The method of claim 1, ~~wherein~~ comprising performing the ion implantation process ~~performed~~ on an active region after the oxidation process is performed by a doze of 1E 11 ion/cm^2 to 1E12 ion/cm^2 in an energy band of 10 KeV to 25 KeV.

5. (Currently Amended) The method of claim 1, ~~wherein~~ comprising using boron ~~is used~~ as an ion that is implanted for controlling the threshold voltage.

6. (New) A method of forming a device isolation film in a semiconductor device, comprising the steps of:

forming a screen oxide film on a semiconductor substrate;

performing an ion implantation for controlling a threshold voltage on the semiconductor substrate;

removing the screen oxide film;

sequentially forming a gate oxide film, a polysilicon film and a pad nitride film on the semiconductor substrate;

forming a trench to define an active region and a device isolation region by sequentially etching a portion of the pad nitride film, the polysilicon film, the gate oxide film and the semiconductor substrate of the device isolation region;

forming a side wall oxidation film at the side wall of the trench by performing an oxidation process for extremely prohibiting ions, which are implanted to control the threshold voltage, from diffusing to the device isolation region;

performing an ion implantation to compensate for ions for controlling the threshold voltage, which are diffused from the active region to the side wall oxidation film by the oxidation process;

removing the pas nitride film; and

forming a device isolation film by burying the oxidation film inside the trench.

7. (New) The method of claim 6, comprising forming the screen oxide film to a thickness in the range of about 50Å to 70Å by a wet oxidation method or a dry oxidation method at a temperature in the range of about 700℃ to 900℃.

8. (New) The method of claim 6, comprising forming the gate oxidation film to a thickness in the range of about 500Å to 700Å by performing an annealing process for 20 minutes to 30 minutes by using N_2 gas at a temperature of about 900℃ to 910℃ after performing a dry or a wet oxidation process at a temperature of about 750℃ to 850℃.

9. (New) The method of claim 6, comprising forming the polysilicon film to a thickness in the range of about 250Å to 500Å by depositing a doped polysilicon film under a pressure of about 0.1 torr to 3 torr in an atmosphere of a PH_3 gas and a Si source gas such as SiH_4 or Si_2H_6 at a temperature of about 500℃ to 550℃.

10. (New) The method of claim 6, comprising forming the pad nitride film to a thickness of about 900Å to 2000Å by a low pressure chemical vapor deposition method.

11. (New) The method of claim 6, comprising forming the side wall oxidation film to perform a rounding treatment on an upper portion or a bottom corner of the trench and to increase an adhesive strength of the oxidation film to be buried inside the trench, at the same time, and forming the film to a thickness in the range of about 50 Å to 100 Å.

12. (New) The method of claim 6, comprising forming the oxidation process by a dry oxidation method at a temperature in the range of about 800 ℃ to 950 ℃.

13. (New) The method of claim 6, comprising performing the ion implantation process on an active region after the oxidation process is performed by a doze of 1E 11 ion/cm^2 to 1E12 ion/cm^2 in an energy band of 10 KeV to 25 KeV.

14. (New) The method of claim 6, comprising using boron as an ion that is implanted for controlling the threshold voltage.